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ABSTRACT OF THE DISCLOSURE

In order to constantly produce a uniform SOI substrate without defect at a low cost by preventing destruction of a porous layer prior to separation of bonded substrates and effecting separation of the bonded substrates securely and easily, in a process for producing a semiconductor substrate comprising forming a non-porous semiconductor layer (13) on a first substrate (10) having porous layers (11, 12) formed on a surface thereof, forming an insulating layer (15) on a surface thereof, bonding the insulating layer (15) to a second substrate (14), and separating the porous layers (11, 12), thereby transferring the insulating layer (15) and the non-porous semiconductor layer (13) onto the surface of the second substrate (14), the first porous layer (11) is formed with a low porosity while the second porous layer is made thin to such extent as to be fragile to easily separate the first and the second substrates.

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